

Amendments to the Specification:

The paragraph starting on page 4, line 22, is amended herein and now reads as follows:

-- The projection exposure system 1 includes an illuminating unit 3 and a projection objective 5. The illuminating unit can, for example, be an excimer laser having a wavelength of less than 250 nm. The projection objective 5 includes a lens arrangement 19 having an aperture diaphragm AP. An optical axis 7 is defined by the lens arrangement 19. Different lens arrangements are explained hereinafter with reference to FIGS. 2 and 3. A mask 9 is mounted between the illuminating unit 3 and the projection objective 5 and the mask is held in the beam path with the aid of a mask holder. Masks 9 used in microlithography have a micrometer-nanometer structure. This structure is imaged on an image plane 13 by means of the projection objective 5 demagnified up to a factor of 10 (demagnified especially by a factor of 4). A substrate 15 or a wafer, which is positioned by a substrate holder 17, is held in the image plane 13. --

On page 5, between lines 12 and 13, please insert the following paragraph:

-- According to another feature of the invention, the illumination unit can be a light source for emitting ultraviolet laser light. -